Please amend claims 4 - 6 as follows:

Claim 4, line 2, change "claim 2" to --claim 15--.

Claim 5, line 2, change "claim 1" to --claim 11 or 15--.

Claim 6, line 2, change "claim 1" to --claim 11 or 15--.

Please add claims 11 - 17 as follows:

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- 11. A fabrication method of a semiconductor device comprising the steps of:
- (a) forming a plurality of projection electrodes on each of a plurality of semiconductor chips;
- (b) applying a thermosetting insulating adhesive to areas of mounting parts where the semiconductor chips are to be mounted on a substrate;
- (c) heating the thermosetting insulating adhesive on the substrate with a half-thermosetting temperature so as to harden the thermosetting insulating adhesive to a half-thermosetting state by beating means and aligning the semiconductor chips to the mounting parts of the substrate at a first stage by a bonding head not-having heating-means;

- (d) moving the substrate to a second stage, while the semiconductor chips on the mounting parts of the substrate are held at their position by the half-thermosetting state of the thermosetting insulating adhesive; and
- (e) thereafter heating the substrate, on which the semiconductor chips are fixed, with a thermosetting temperature of the thermosetting insulating adhesive.
- 12. A fabrication method according to claim 11, wherein in the heating step (c), heating the thermosetting insulating adhesive is performed by a heat plate on which the substrate mounting the semiconductor chips is placed.
- 13. A fabrication method according to claim 11, wherein in the heating step (e), while heating the thermosetting insulating adhesive on the mounting parts of the substrate, a pressure is applied to the semiconductor chips.
- 14. A fabrication method according to claim 13, wherein in the heating step (e), heating the thermosetting insulating adhesive is performed by a heat block having a plurality of pressing/heating heads each of which is provided on the heat block corresponding to the mounting parts of the substrate.

A fabrication method of a semiconductor device comprising the steps of:

(a) A fabrication method of a semiconductor device comprising the steps of:

forming a plurality of projection electrodes on each of a plurality of semiconductor chips;

- (b) applying a thermosetting insulating adhesive to areas of mounting parts where the semiconductor chips are to be mounted on a substrate;
- (c) heating the thermosetting insulating adhesive on the substrate with a half-thermosetting temperature so as to harden the thermosetting insulating adhesive to a half-thermosetting state by heating means and, concurrently, aligning the semiconductor chips to the mounting parts of the substrate at a first stage and performing a first fixing of the semiconductor chips with a first pressure by a bonding head not having heating means;
- (d) moving the substrate to a second stage, while the semiconductor chips on the mounting parts of the substrate are held at their position by the half-thermosetting state of the thermosetting insulating adhesive; and
- (e) thereafter heating the substrate, on which the semiconductor chips are fixed, with a thermosetting temperature of the thermosetting insulating adhesive, and performing a second fixing of the semiconductor chips with a second pressure, wherein the second pressure for performing the second fixing of the semiconductor chips is greater than the first pressure for performing the first fixing of the semiconductor chips.
- 16. A fabricating method according to claim 15, wherein in the heating step (c), heating the thermosetting insulating adhesive is performed by a heat plate on which the substrate mounting the semiconductor chips is placed.

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A fabrication method according to claim 15, wherein in the heating step (e), heating the thermosetting insulating adhesive and performing the second fixing of the semiconductor chips are performed by a heat block having a plurality of pressing/heating heads each of which is provided on the heat block corresponding to the mounting parts of the substrate.

REMARKS

Claims 1, 2 and 7 have been cancelled without prejudice or disclaimer.

Claims 11 - 17 have been added, and claims 4 - 6 have been amended in order to more particularly point out, and distinctly claim the subject matter to which the applicants regard as their invention. It is believed that this Amendment is fully responsive to the Office Action dated December 16, 1997.

<u>First</u>, the Examiner objects to the drawings for the reasons that the subject matters set forth in clauses (b) and (c) in claim 1 and in claim 2, both currently on file, are <u>not</u> shown in the drawings.